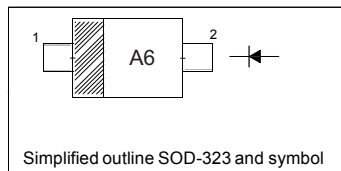


Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode


Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

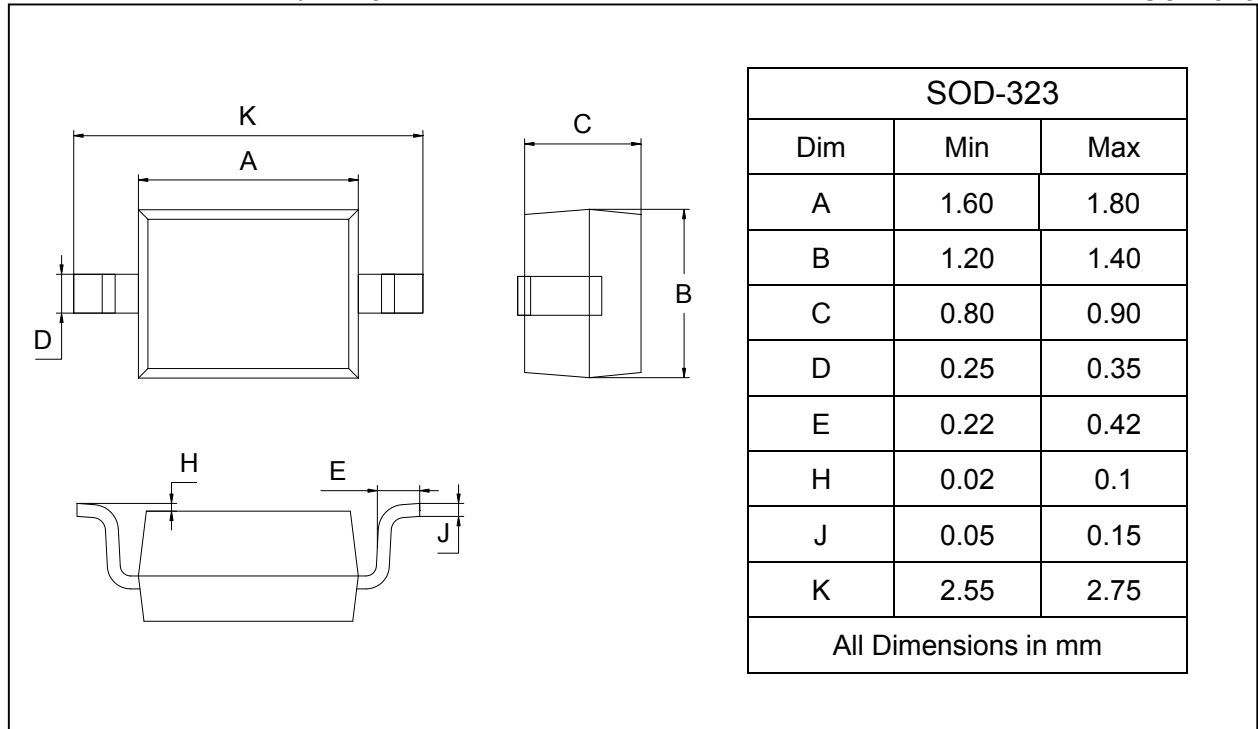
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	71	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Non-Repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	2.0	A
Power Dissipation	P_d	200	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	$^{\circ}\text{C/W}$
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^{\circ}\text{C}$

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

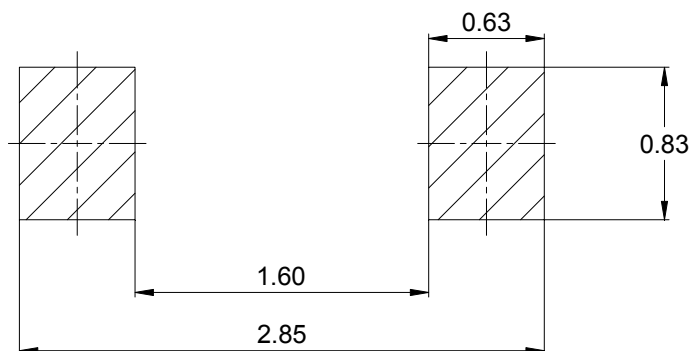
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V_{F1}			0.715	V	$I_F=1\text{mA}$
	V_{F2}			0.855	V	$I_F=10\text{mA}$
	V_{F3}			1.0	V	$I_F=50\text{mA}$
	V_{F4}			1.25	V	$I_F=150\text{mA}$
Reverse current	I_{R1}			1	μA	$V_R=75\text{V}$
	I_{R2}			25	nA	$V_R=20\text{V}$
Capacitance between terminals	C_T			2	pF	$V_R=0\text{V}, f=1\text{MHz}$
Reverse recovery time	t_{rr}			4	ns	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1I_R, R_L=100\Omega$

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

Typical Characteristics

